

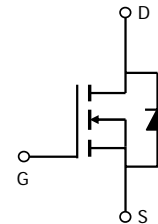
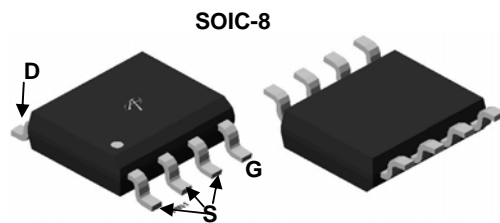
General Description

The AO4454L is fabricated with SDMOS™ trench technology that combines excellent $R_{DS(ON)}$ with low gate charge. The result is outstanding efficiency with controlled switching behavior. This universal technology is well suited for PWM, load switching and general purpose applications.

Product Summary

| | |
|----------------------------------|--------|
| V_{DS} | 100V |
| I_D (at $V_{GS}=10V$) | 6.5A |
| $R_{DS(ON)}$ (at $V_{GS}=10V$) | < 36mΩ |
| $R_{DS(ON)}$ (at $V_{GS} = 7V$) | < 43mΩ |

100% UIS Tested
100% R_g Tested



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

| Parameter | Symbol | Maximum | Units |
|---|------------------|------------------|-------|
| Drain-Source Voltage | V_{DS} | 100 | V |
| Gate-Source Voltage | V_{GS} | ±25 | V |
| Continuous Drain Current | I_D | $T_A=25^\circ C$ | A |
| | | $T_A=70^\circ C$ | |
| Pulsed Drain Current ^C | I_{DM} | 46 | A |
| Avalanche Current ^C | I_{AS}, I_{AR} | 28 | A |
| Avalanche energy $L=0.1mH$ ^C | E_{AS}, E_{AR} | 39 | mJ |
| Power Dissipation ^B | P_D | $T_A=25^\circ C$ | W |
| | | $T_A=70^\circ C$ | |
| Junction and Storage Temperature Range | T_J, T_{STG} | -55 to 150 | °C |

Thermal Characteristics

| Parameter | Symbol | Typ | Max | Units |
|--|-----------------|--------------|-----|-------|
| Maximum Junction-to-Ambient ^A | $R_{\theta JA}$ | 31 | 40 | °C/W |
| Maximum Junction-to-Ambient ^{A,D} | | Steady-State | 59 | 75 |
| Maximum Junction-to-Lead | $R_{\theta JL}$ | 16 | 24 | °C/W |

Electrical Characteristics (T_J=25°C unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|-----------------------------|---------------------------------------|---|------|----------|----------|-------|
| STATIC PARAMETERS | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | I _D =250μA, V _{GS} =0V | 100 | | | V |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =100V, V _{GS} =0V T _J =55°C | | | 10 50 | μA |
| I _{GSS} | Gate-Body leakage current | V _{DS} =0V, V _{GS} = ±25V | | | 100 | nA |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =250μA | 2.8 | 3.4 | 4 | V |
| I _{D(ON)} | On state drain current | V _{GS} =10V, V _{DS} =5V | 46 | | | A |
| R _{DS(ON)} | Static Drain-Source On-Resistance | V _{GS} =10V, I _D =6.5A T _J =125°C | | 30 56 | 36 67 | mΩ |
| | | V _{GS} =7V, I _D =6A | | 35.5 | 43 | mΩ |
| g _{FS} | Forward Transconductance | V _{DS} =5V, I _D =6.5A | | 20 | | S |
| V _{SD} | Diode Forward Voltage | I _S =1A, V _{GS} =0V | | 0.68 | 1 | V |
| I _S | Maximum Body-Diode Continuous Current | | | | 4 | A |
| DYNAMIC PARAMETERS | | | | | | |
| C _{iss} | Input Capacitance | V _{GS} =0V, V _{DS} =50V, f=1MHz | 950 | 1180 | 1450 | pF |
| C _{oss} | Output Capacitance | | 77 | 110 | 145 | pF |
| C _{rss} | Reverse Transfer Capacitance | | 21 | 36 | 50 | pF |
| R _g | Gate resistance | V _{GS} =0V, V _{DS} =0V, f=1MHz | 0.35 | 0.7 | 1.05 | Ω |
| SWITCHING PARAMETERS | | | | | | |
| Q _{g(10V)} | Total Gate Charge | V _{GS} =10V, V _{DS} =50V, I _D =6.5A | 15 | 19 | 23 | nC |
| Q _{gs} | Gate Source Charge | | 5.5 | 7 | 8.5 | nC |
| Q _{gd} | Gate Drain Charge | | 3.5 | 6.3 | 9 | nC |
| t _{D(on)} | Turn-On DelayTime | V _{GS} =10V, V _{DS} =50V, R _L =6.7Ω, R _{GEN} =3Ω | | 10 | | ns |
| t _r | Turn-On Rise Time | | | 7.2 | | ns |
| t _{D(off)} | Turn-Off DelayTime | | | 15 | | ns |
| t _f | Turn-Off Fall Time | | | 7 | | ns |
| t _{rr} | Body Diode Reverse Recovery Time | I _F =6.5A, dI/dt=500A/μs | 11 | 16 | 21 | ns |
| Q _{rr} | Body Diode Reverse Recovery Charge | I _F =6.5A, dI/dt=500A/μs | 35 | 50 | 65 | nC |

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150°C, using ≤ 10s junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J=25°C.

D. The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of T_{J(MAX)}=150°C. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

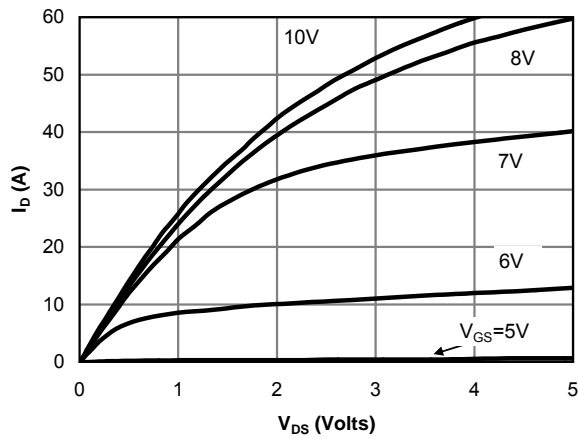


Fig 1: On-Region Characteristics (Note E)

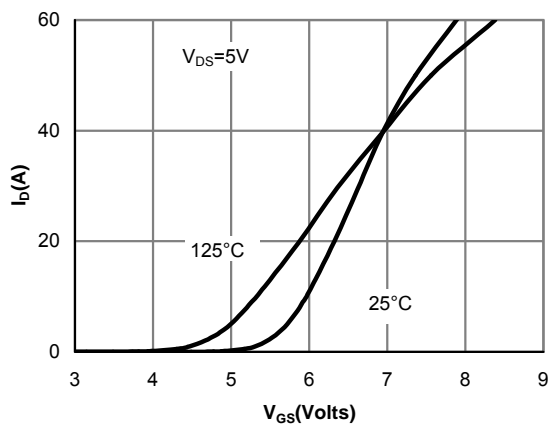


Figure 2: Transfer Characteristics (Note E)

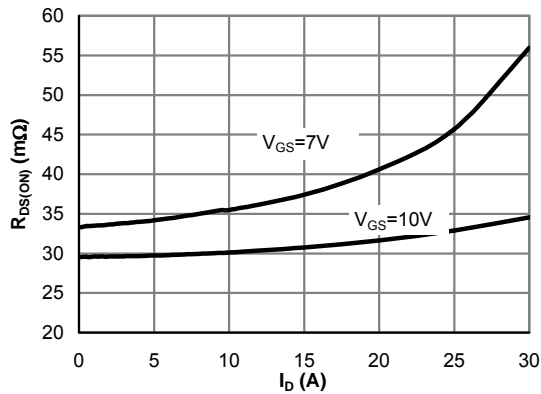


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

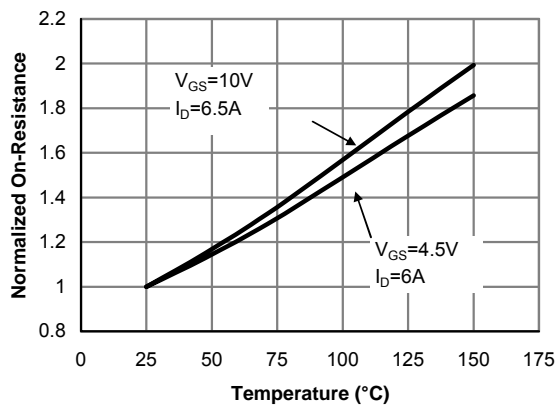


Figure 4: On-Resistance vs. Junction Temperature (Note E)

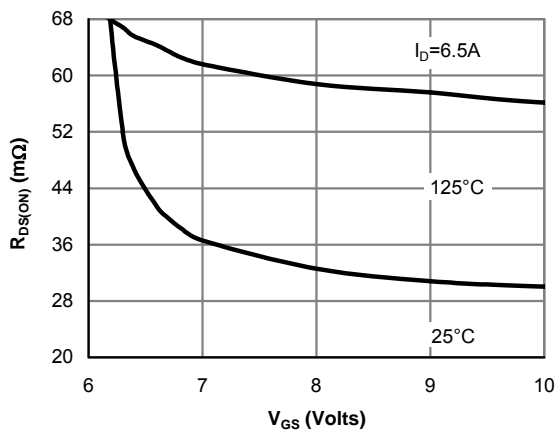


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

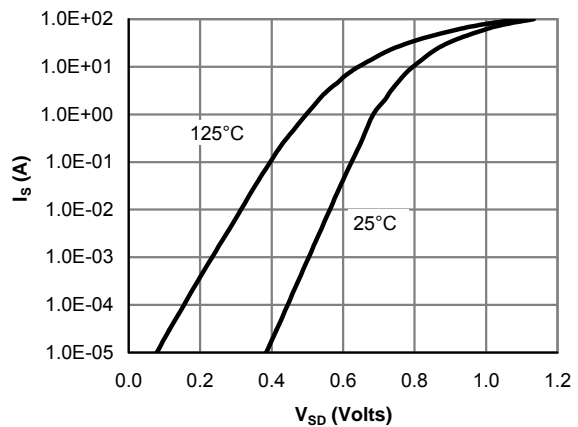


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

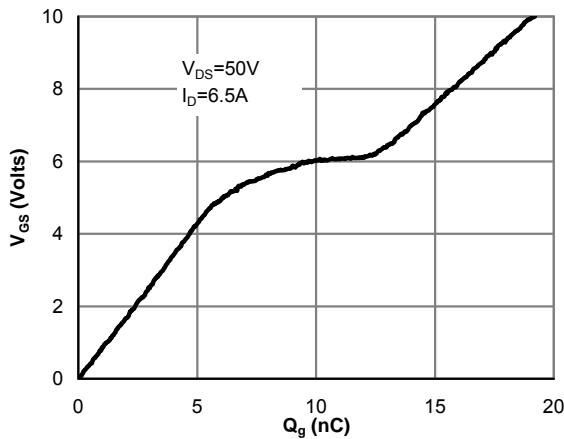


Figure 7: Gate-Charge Characteristics

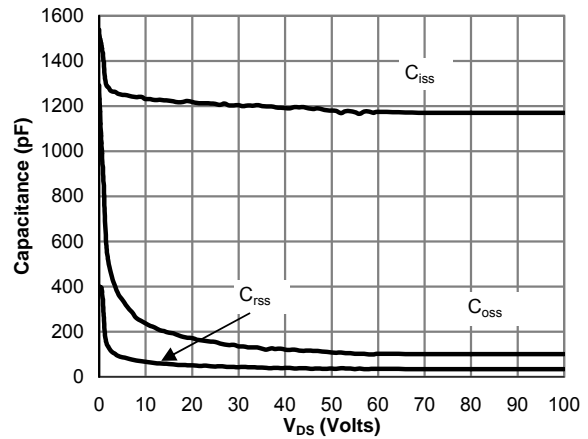


Figure 8: Capacitance Characteristics

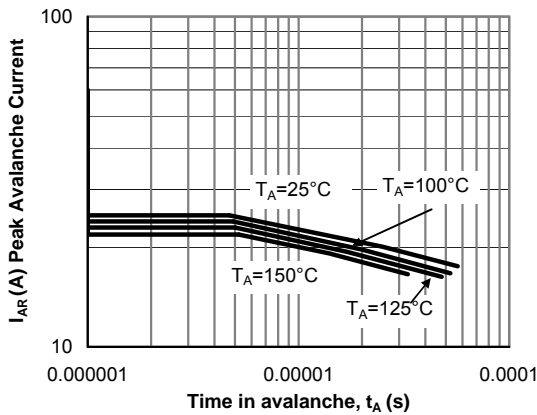


Figure 9: Single Pulse Avalanche capability (Note C)

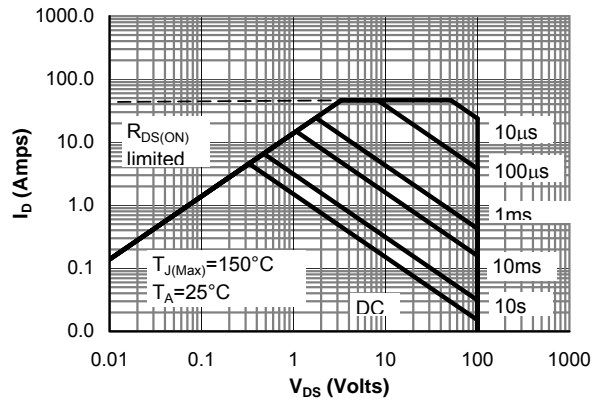


Figure 10: Maximum Forward Biased Safe Operating Area (Note F)

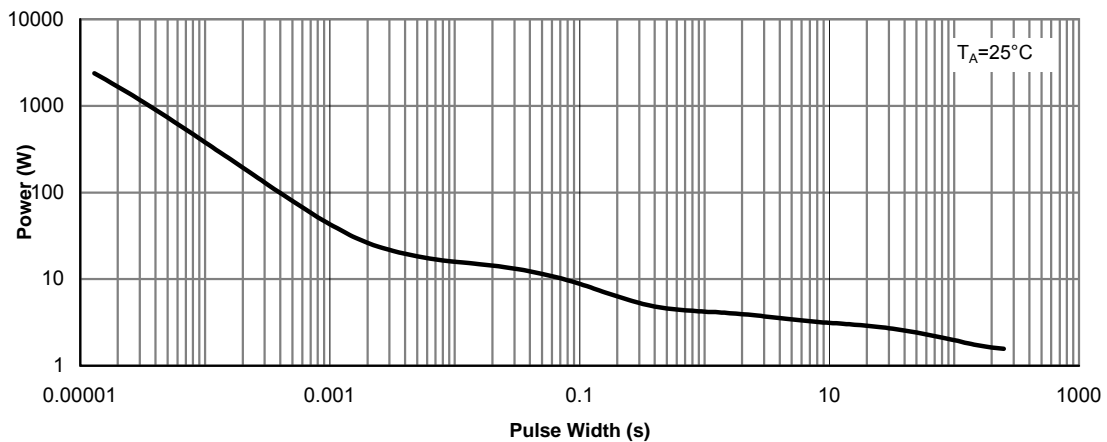


Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

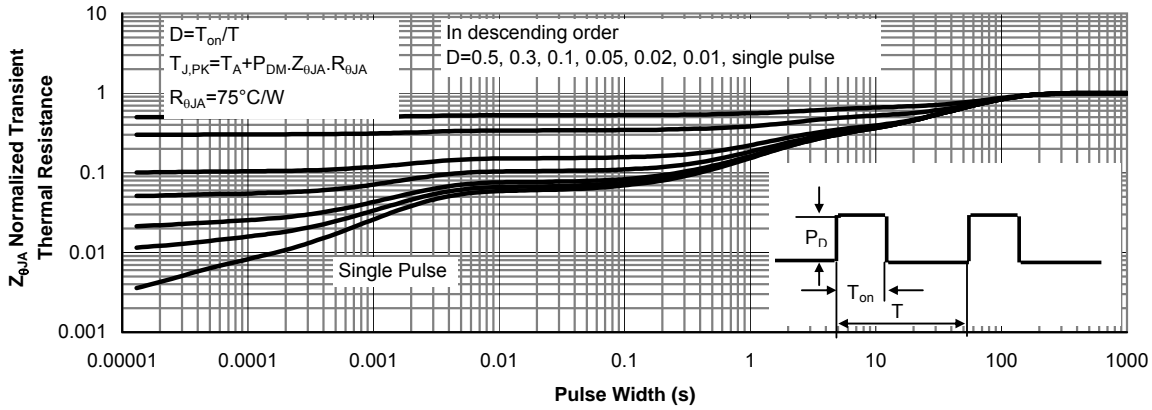


Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)

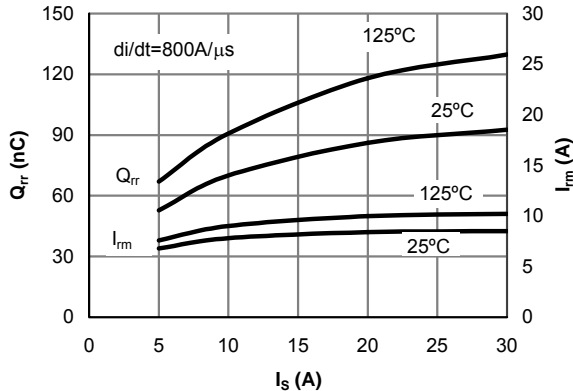


Figure 13: Diode Reverse Recovery Charge and Peak Current vs. Conduction Current

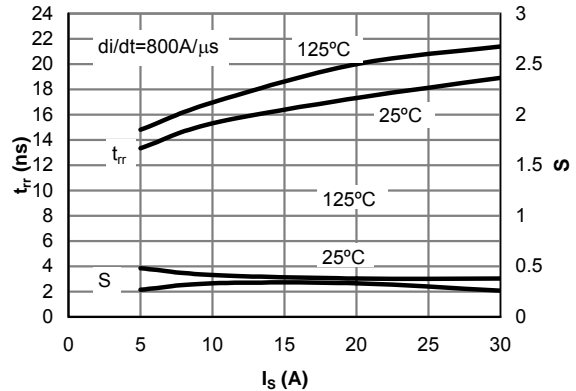


Figure 14: Diode Reverse Recovery Time and Softness Factor vs. Conduction Current

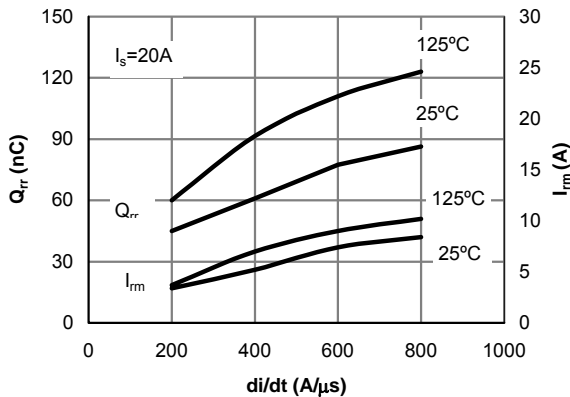


Figure 15: Diode Reverse Recovery Charge and Peak Current vs. di/dt

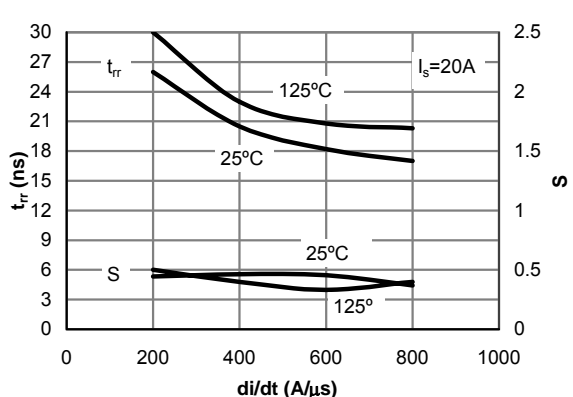
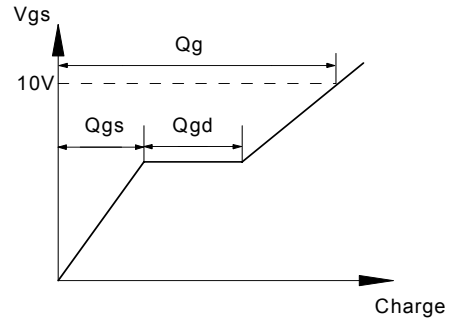
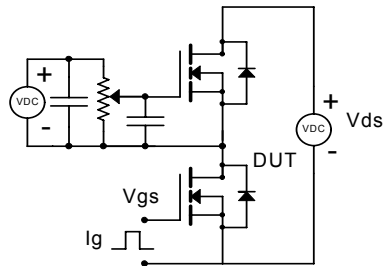
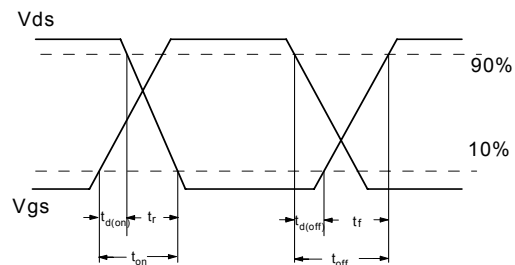
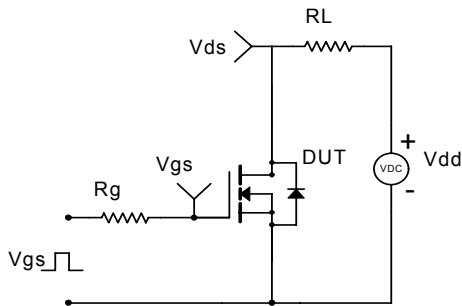


Figure 16: Diode Reverse Recovery Time and Softness Factor vs. di/dt

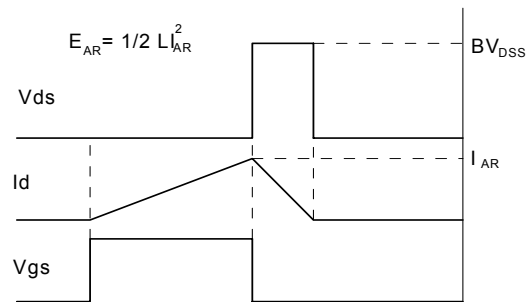
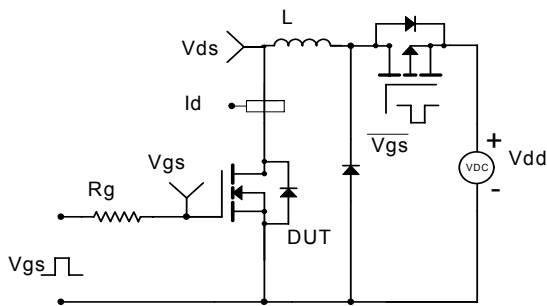
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

